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U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
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L. J. M-E.	Kim, T.S. et al., "Intergration of Organosilicate Glasses (OSGs) In High Performance Copper Interconnects", Advanced Metallization Conference 2001, pp. 25-31, (October 2001)
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Examiner Lynette T. Umeg-Eumini	Date Considered 12/16/2005
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